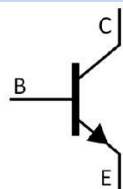


Silicon NPN transistor in a SOT-23 Plastic Package.

High frequency.

High frequency amplifier.



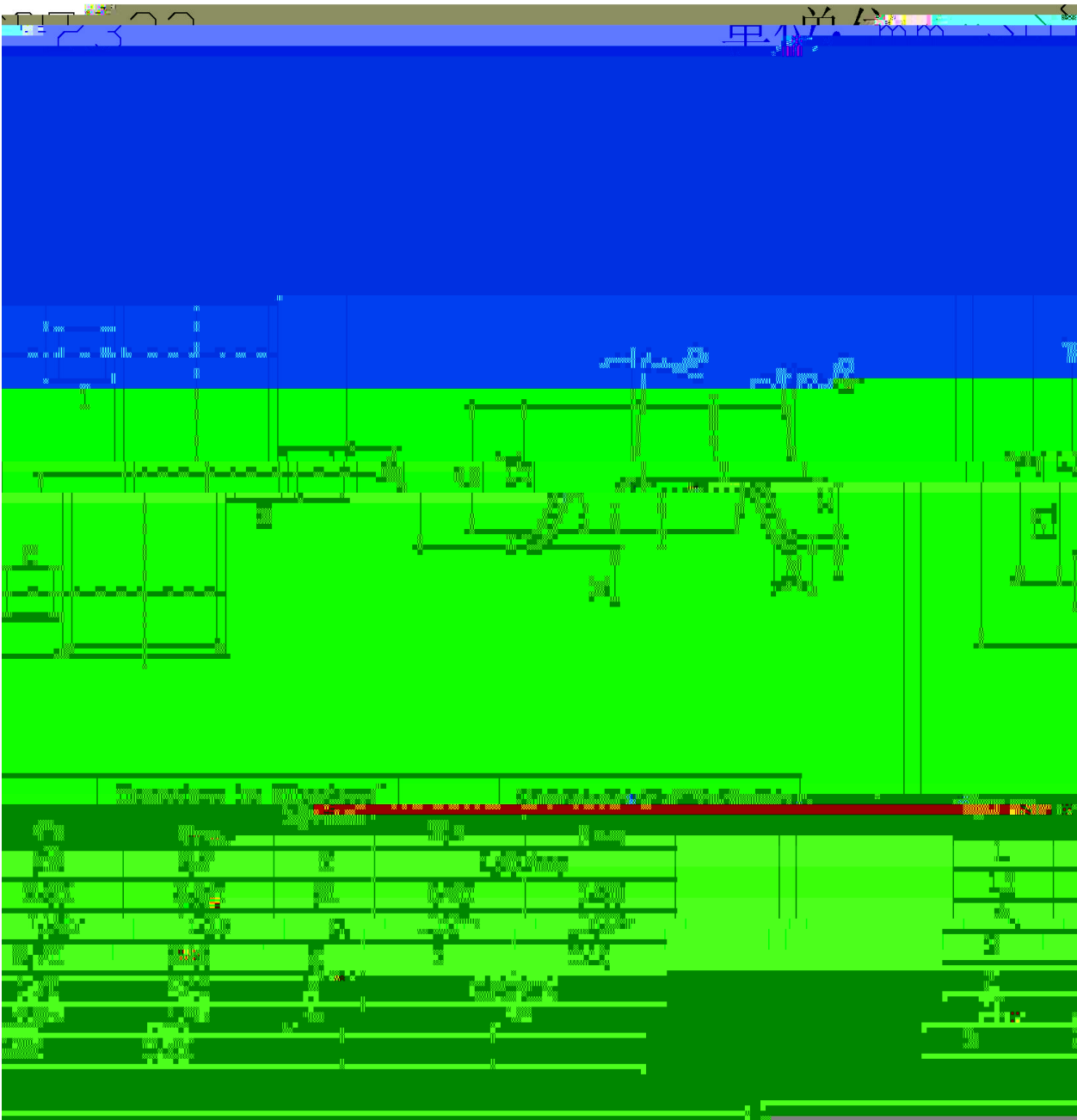
PIN 1 Base PIN 2 Emitter PIN 3 Collector

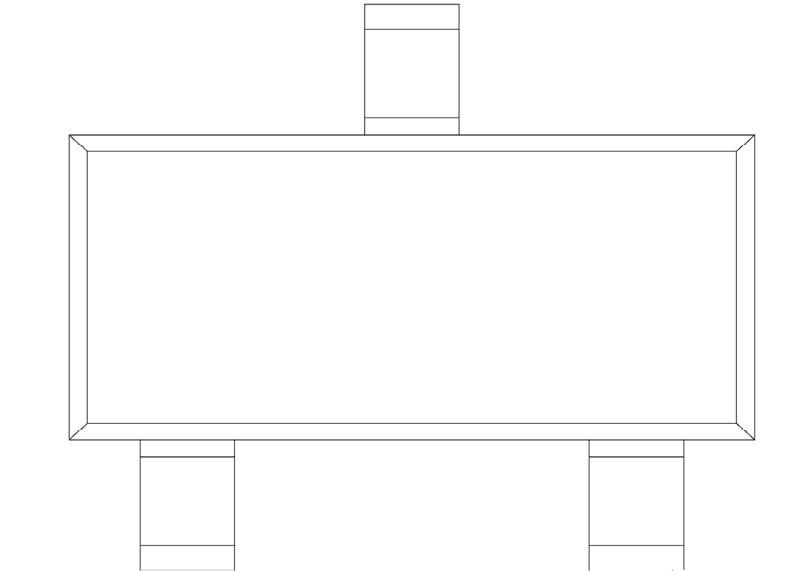
h _{FE} Classifications Symbol	R	O	Y
h _{FE} Range	40-80	60-120	90-180
Marking	HH5R	HH5O	HH5Y

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current	I_C	20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=30V$ $I_E=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	40	90	180	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA$ $I_B=1.0mA$		0.1	0.3	V
Transition Frequency	f_T	$I_C=1.0mA$ $V_{CE}=6.0V$	400	600		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=6.0V$ $I_E=0$ $f=1.0MHz$		1.0		pF
Time Constant	$C_c, r_{bb'}$	$V_{CB}=6.0V$ $I_C=1.0mA$ $f=31.9MHz$		12		Ps
Noise Figure	NF	$V_{CE}=6.0V$ $I_C=1.0mA$ $f=100MHz$ $R_s=50\Omega$		3.0		dB



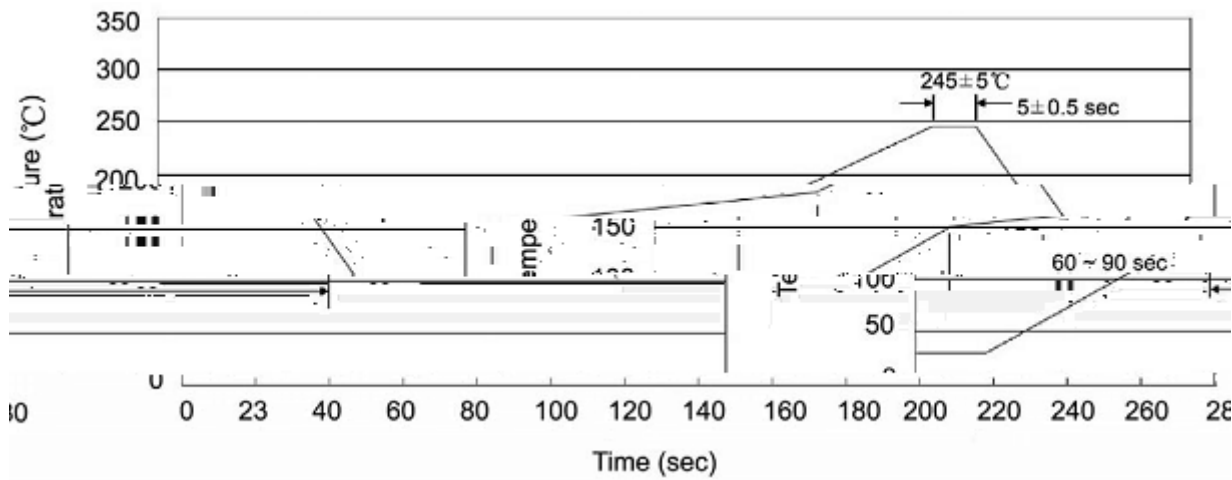




Note:

	Company Code
H5	Product Type Code
	h

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

245 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:245 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Units 包装数量

Dimension 包装尺寸 (unit: mm DPDQs